

ABSTRACT

An increased number of fuses per area are provided in this semiconductor device while complying with the predetermined distance between the fuses. The device having a first patterned, conductive interconnect plane on a passivated substrate; a second patterned, conductive interconnect plane on the first patterned, conductive passivated interconnect plane; contact devices for selectively electrically contact-connecting the patterned, conductive interconnect planes to one another; a fuse device in a nonpassivated section of the second patterned, conductive interconnect plane with predetermined fuse regions for selectively linking interconnects; the fuse device being divided into fuse modules with fuse pairs and the fuse regions thereof at a predetermined distance from one another, which can be linked to a predetermined potential via a central interconnect.

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